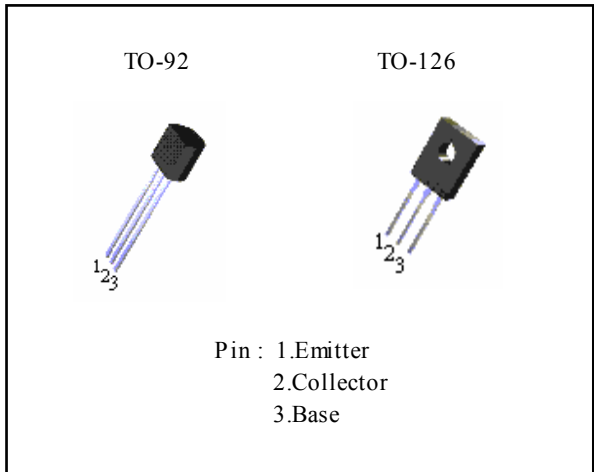


PNP Epitaxial Silicon Transistor

**AUDIO FREQUENCY POWER AMPLIFIER
LOW SPEED SWITCHING**

- Complement to PJD882
- PW 10μs, Duty Cycle 50%
- Pulse Test PW 350μs, Duty Cycle 2%



ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Bias Voltage	V _{EBO}	-5	V
Collector Current (DC)	I _C	-2	A
*Collector Current (Pulse)	I _C	-5	A
Base Current (DC)	I _B	-0.6	A
Collector Dissipation (Ta=25°C)	P _C	-	W
Collector Dissipation (Tc=25°C)	P _C	1	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-	°C
		55~150	

ORDERING INFORMATION

Device	Operating Temperature	Package
PJB772SCT	-20°C ~ +85°C	TO-92
PJB772CK		TO-126

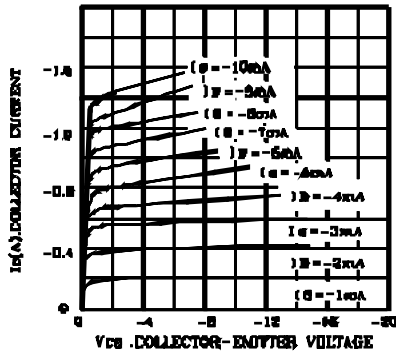
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Characteristics	Symbol	Test condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CB0}	V _{CB} =-30V, I _E =0			-1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-3V, I _C =0			-1	μA
*DC Current Gain	h _{FE1}	V _{CE} =-2V, I _C =-20mA	30	220		
	h _{FE2}	V _{CE} =-2V, I _C =-1A	60	160	400	
*Collector Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-2A, I _B =-0.2A		-0.3	-0.45	V
Voltage	V _{BE(SAT)}	I _C =-2A, I _B =-0.2A		-1.0	-2.0	V
*Base Emitter Saturation Voltage	f _T	V _{CE} =-5V, I _C =0.1A		80		MHz
Current Gain Bandwidth Product	Cob	V _{CB} =-10V, I _E =0		55		pF
Output Capacitance		f=1MHz				
Noise Figure	NF	V _{CE} =10V, I _C =1mA		4		dB
		R _S =10K, f=1KHz				

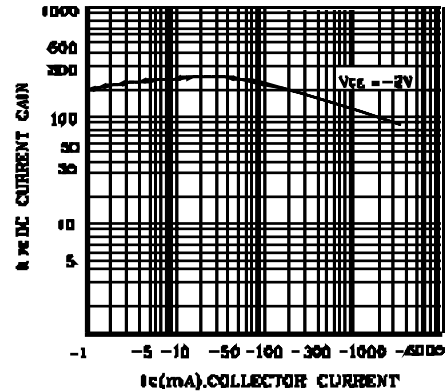
h_{FE}(2) CLASSIFICATION

Classification	R	O	Y	G
h _{FE} (2)	60-120	100-200	160-320	200-400

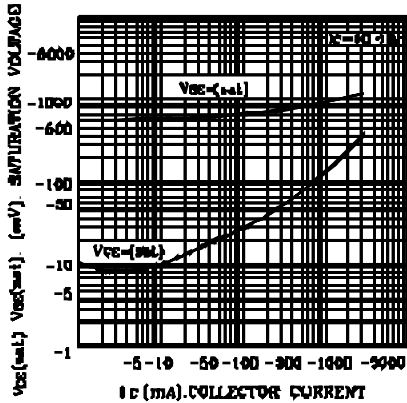
STATIC CHARACTERISTIC



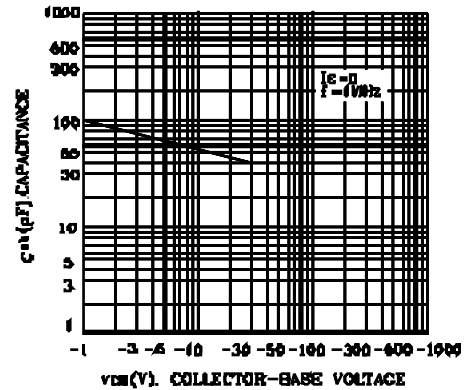
DC CURRENT GAIN



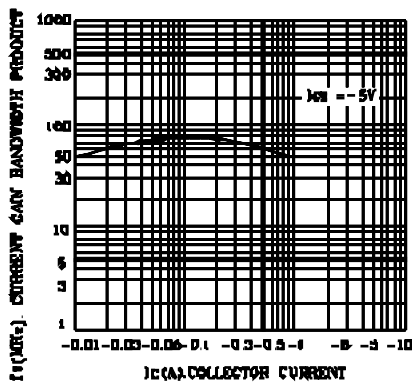
BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



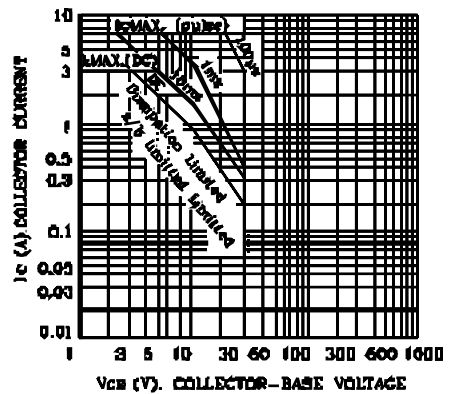
COLLECTOR OUTPUT CAPACITANCE



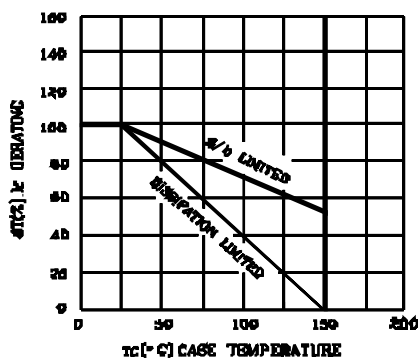
CURRENT GAIN-BANDWIDTH PRODUCT



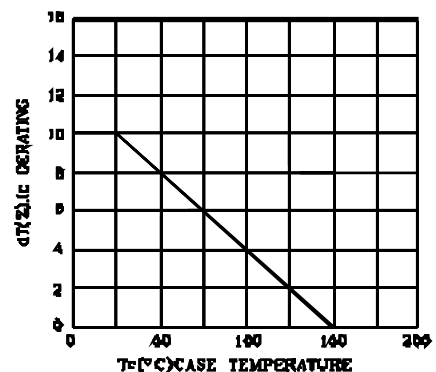
SAFE OPERATING AREAS



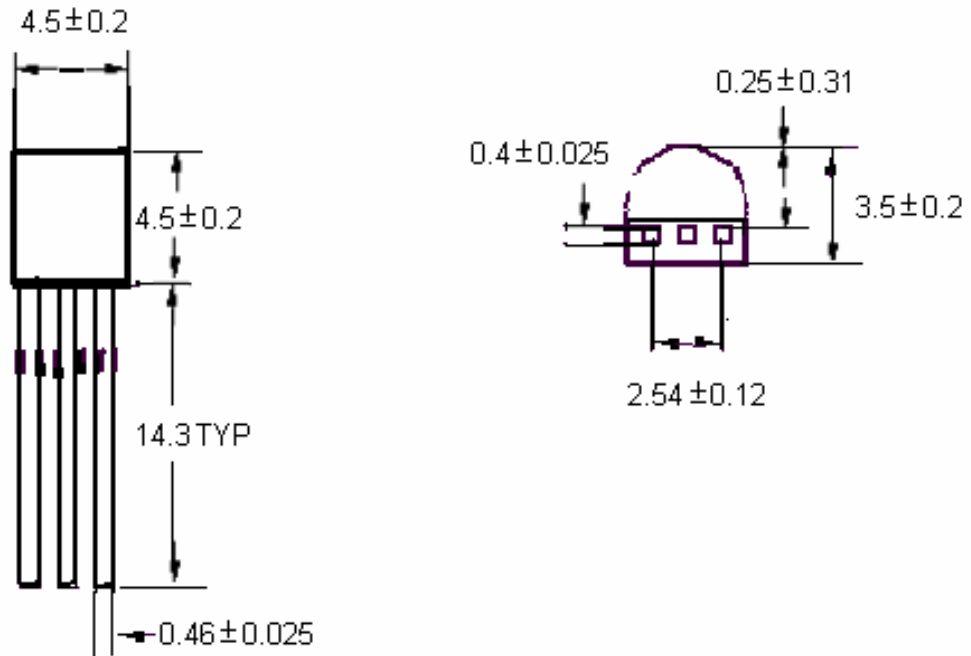
DERATING CURVE OF SAFE OPERATING AREAS



POWER DERATING



TO-92 Unit:mm



TO-126 Unit:mm

